

Supplementary Information

Sodium Bismuth Dichalcogenides: Candidates of Ferroelectric High-mobility Semiconductors for Multifunctional Applications

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Table S1. Fitted parameters A, B, C in Landau-Ginzburg expansion.

	A	B	C
NaBiS ₂	-5.97	-29.27	771.26
NaBiSe ₂	-5.26	-98.23	1223.03

Table S2. Calculated effective mass m^* (with m_0 being the static electron mass), deformation potential E_i , elastic modulus C and carrier mobility u along the x and y directions.

	m_x^*/m_0	m_y^*/m_0	E_{ix} (eV)	E_{iy}	$C_{x,3D}$ (J · m ⁻³)	$C_{y,3D}$	$u_{x,3D}$ (10 ³ cm ² · V ⁻¹ · s ⁻¹)	$u_{y,3D}$
3% biaxial strain NaBiS ₂	0.21	0.38	-7.47	-4.52	0.56×10^{11}	0.50×10^{11}	3.04	1.68
Na _{0.5} K _{0.5} BiS ₂	0.37	0.42	-6.37	-3.93	0.38×10^{11}	0.33×10^{11}	0.69	1.14
NaBi _{0.75} V _{0.25} S ₂	0.26	0.43	-4.61	-6.11	0.44×10^{11}	0.36×10^{11}	3.68	0.49

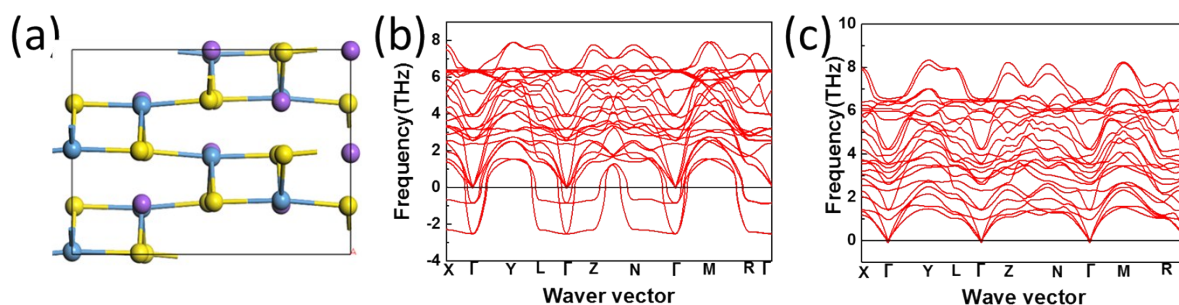


Figure S1. (a)Antiferroelectric configuration of NaBiS₂. Phonon dispersion of (b)paraeelectric and (c)FE phase for NaBiS₂ calculated by using Phonopy.

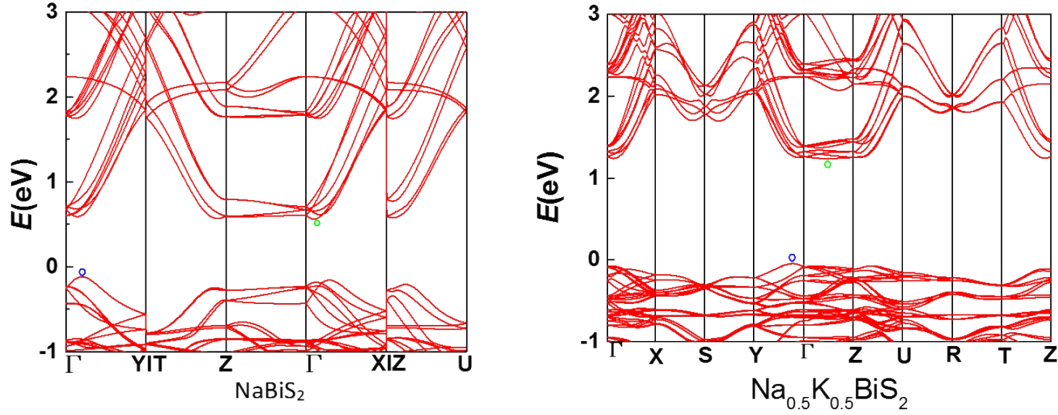


Figure S2. Bandstructures of NaBiS₂ and Na_{0.5}K_{0.5}BiS₂ by using PBE+SOC.

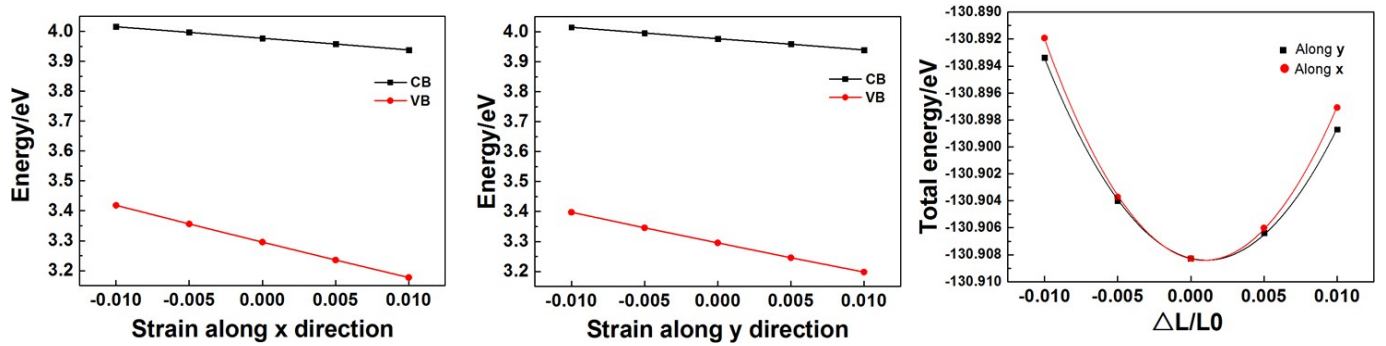


Figure S3. E_1 obtained by linearly fitting the energy shift of the band energy position (CBM and VBM) with respect to a small lattice strain along the $-x$ (left) and $-y$ (middle) direction, and C_{111} calculated based on the quadratic relation between the total energy and lattice dilations under strain (right).

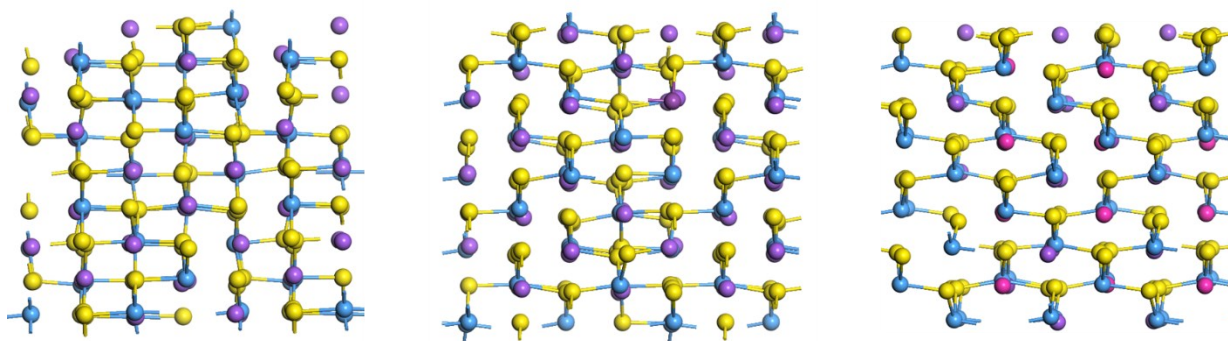


Figure S4. Snapshot of the equilibrium structures at 300K for pristine NaBiS₂ (left), NaBiS₂ upon a 3% biaxial strain at xy plane (middle), and Na_{0.5}K_{0.5}BiS₂ (right) at the end of 10ps of ab initio MD simulation with a canonical ensemble (time step is set as 1fs).